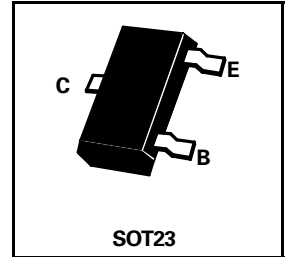


SOT23 NPN SILICON PLANAR GENERAL PURPOSE TRANSISTORS

ISSUE 6 - JANUARY 1997

BC846	BC847
BC848	BC849
BC850	

PARTMARKING DETAILS		COMPLEMENTARY TYPES	
BC846A-Z1A	BC848B-1K	BC846	BC856
BC846B-1B	BC848C-Z1L	BC847	BC857
BC847A-Z1E	BC849B-2B	BC848	BC858
BC847B-1F	BC849C-2C	BC849	BC859
BC847C-1GZ	BC850B-2FZ	BC850	BC860
BC848A-1JZ	BC850C-Z2G		



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	BC846	BC847	BC848	BC849	BC850	UNIT
Collector-Base Voltage	V _{CBO}	80	50	30	30	50	V
Collector-Emitter Voltage	V _{CES}	80	50	30	30	50	V
Collector-Emitter Voltage	V _{CEO}	65	45	30	30	45	V
Emitter-Base Voltage	V _{EBO}	6		5			V
Continuous Collector Current	I _C	100					mA
Peak Collector Current	I _{CM}	200					mA
Peak Base Current	I _{BM}	200					mA
Peak Emitter Current	I _{EM}	200					mA
Power Dissipation at T _{amb} =25°C	P _{tot}	330					mW
Operating and Storage Temperature Range	T _j :T _{stg}	-55 to +150					°C

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL		BC846	BC847	BC848	BC849	BC850	UNIT	CONDITIONS.
Collector Cut-Off Current	I_{CBO}	Max	15					nA	$V_{CB} = 30V$
		Max	5					μA	$V_{CB} = 30V$ $T_{amb}=150^{\circ}C$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	Typ	90					mV	$I_C=10mA$,
		Max.	250					mV	$I_B=0.5mA$
		Typ	200					mV	$I_C=100mA$,
		Max.	600					mV	$I_B=5mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	Typ	300					mV	$I_C=10mA^*$
		Max.	600					mV	
		Typ	700					mV	$I_C=10mA$,
Base-Emitter Voltage	V_{BE}	Typ	900					mV	$I_B=0.5mA$
		Max.						mV	$I_C=100mA$,
		Min						mV	$I_B=5mA$
		Typ						mV	$I_C=2mA$
Base-Emitter Voltage	V_{BE}	Max						mV	$V_{CE}=5V$
		Min						mV	
		Max						mV	
Base-Emitter Voltage	V_{BE}	Min						mV	$I_C=10mA$
		Max						mV	$V_{CE}=5V$

* Collector-Emitter Saturation Voltage at $I_C = 10mA$ for the characteristics going through the operating point $I_C = 11mA$, $V_{CE} = 1V$ at constant base current.

BC846	BC847
BC848	BC849
BC850	

ELECTRICAL CHARACTERISTICS (Continued)

PARAMETER	SYMBOL		BC846	BC847	BC848	BC849	BC850	UNIT	CONDITIONS.
Static Forward Current Ratio	Group VI	h _{FE}	Min	75	75	75	—	—	I _C =2mA, V _{CE} =5V
			Typ	110	110	110	—	—	
			Max	150	150	150	—	—	
	Group A	h _{FE}	Typ	90	90	90	—	—	I _C =0.01mA, V _{CE} =5V
			Min	110	110	110	—	—	I _C =2mA, V _{CE} =5V
			Typ	180	180	180	—	—	
			Max	220	220	220	—	—	
	Group B	h _{FE}	Typ	120	120	120	—	—	I _C =100mA, V _{CE} =5V
			Typ	150					I _C =0.01mA, V _{CE} =5V
			Min	200					I _C =2mA, V _{CE} =5V
			Typ	290					
			Max	450					
		Typ	200	200	200	—	—	I _C =100mA, V _{CE} =5V	
Group C	h _{FE}	Typ.	—	270	270	270	270	I _C =0.01mA, V _{CE} =5V	
		Min	—	420	420	420	420	I _C =2mA, V _{CE} =5V	
		Typ	—	500	500	500	500		
		Max	—	800	800	800	800		
		Typ	—	—	400	—	—	I _C =100mA, V _{CE} =5V	
Transition Frequency	f _T	Typ	300					MHz	I _C =10mA, V _{CE} =5V f=100MHz
Collector-Base Capacitance	C _{obo}	Typ	2.5					pF	V _{CB} =10V f=1MHz
		Max	4.5					pF	
Emitter-Base Capacitance	C _{ib0}	Typ	9					pF	V _{EB} =0.5V f=1MHz
Noise Figure	N	Typ	2	2	2	1.2	1	dB	V _{CE} = 5V, I _C =200μA, R _C =2kΩ, f=1kHz, Δf=200Hz
		Max	10	10	10	4	4	dB	
		Typ	—	—	—	1.2	1	dB	V _{CE} = 5V, I _C =200μA, R _C =2kΩ, f=30Hz to 15kHz at -3dB points
		Max	—	—	—	4	3	dB	
Equivalent Noise Voltage	e _n	Max.	—	—	—	110	110	nV	V _{CE} = 5V, I _C =200μA, R _C =2kΩ, f=10Hz to 50Hz at -3dB points

Spice parameter data is available upon request for this device

BC846	BC847
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BC850	

ELECTRICAL CHARACTERISTICS (Continued)

PARAMETER		SYMBOL		BC846	BC847	BC848	BC849	BC850	UNIT	CONDITIONS.	
Dynamic Characteristics	Group VI	h_{ie}	Min	0.4	0.4	0.4	—	—	k Ω	$V_{CE}=5V$ $I_C=2mA$	
			Typ	1.2	1.2	1.2	—	—	k Ω		
			Max	2.2	2.2	2.2	—	—	k Ω		
			Group A	Min	1.6	1.6	1.6	—	—		k Ω
				Typ	2.7	2.7	2.7	—	—		k Ω
	Group B	Max	4.5	4.5	4.5	—	—	k Ω			
		Group C	Min	3.2					k Ω		
	Typ		4.5					k Ω			
	Max	8.5					k Ω				
	Group VI	h_{re}	Typ	2.5	2.5	2.5	—	—	$\times 10^{-4}$		
Typ			1.5	1.5	1.5	—	—	$\times 10^{-4}$			
Typ			2	2	2	2	2	$\times 10^{-4}$			
Typ			—	—	3	3	3	$\times 10^{-4}$			
Typ			—	—	3	3	3	$\times 10^{-4}$			
Group VI	h_{fe}	Min	75	75	75	—	—				
		Typ	110	110	110	—	—				
		Max	150	150	150	—	—				
		Group A	Min	125	125	125	—	—			
			Typ	220	220	220	—	—			
		Max	260	260	260	—	—				
		Group B	Min	240							
			Typ	330							
		Group C	Max	500							
			Min	—	450	450	450	450			
		Typ	—	600	600	600	600				
		Max	—	900	900	900	900				
Group VI	h_{oe}	Typ	20	20	20	—	—	μs			
		Max	40	40	40	—	—	μs			
		Group A	Typ	18	18	18	—	—	μs		
			Max	30	30	30	—	—	μs		
		Group B	Typ	30					μs		
			Max	60					μs		
		Group C	Typ	—	—	60	60	60	μs		
			Max	—	—	110	110	110	μs		

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